

Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

Complete if Known	
Application Number	Unknown 10/789,041
Filing Date	Even Date Herewith 2/27/04
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2818
Examiner Name	Unknown PHAN

Sheet 1 of 8

Attorney Docket No: 1303.058US2

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
TP	US020109158	08/15/2002	Forbes, Leonard , et al.	257	224	02/09/2001
	US20020027264A1	03/07/2002	Forbes, Leonard , et al.	257	662	08/08/2001
	US20020155688	10/24/2002	Ahn, Kie Y., et al.	438	592	04/20/2001
	US20020155689	10/24/2002	Ahn, Kie Y., et al.	29	76	02/11/2002
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	US20020036939A1	03/28/2002	Tsai, Wen-Jer , et al.	365	201	08/30/2001
	US20020074565A1	06/20/2002	Flagan, R. C., et al.	257	200	06/29/2001
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✓	US-5,627,785	05/06/1997	Gilliam, Gary R., et al.	365	189.01	03/15/1996

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Examiner Name	Unknown PHA/V

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TP	US-5,740,104	04/14/1998	Forbes, Leonard	365	185.03	01/29/1997
	US-5,768,192	06/16/1998	Eitan, Boaz	365	185.24	07/23/1996
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	US-5,828,605	10/27/1998	Peng, K., et al.	365	185.29	10/14/1997
	US-5,852,306	12/22/1998	Forbes, Leonard	257	315	01/29/1997
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	US-5,886,368	03/23/1999	Forbes, Leonard, et al.	257	77	07/29/1997
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	US-6,115,281	09/05/2000	Aggarwal, S., et al.	365	145	09/11/1998
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TP	US-6,232,643	05/15/2001	Forbes, Leonard , et al.	257	405	11/13/1997
	US-6,238,976	05/29/2001	Noble, Wendell P., et al.	438	259	02/27/1998
	US-6,243,300	06/05/2001	Sunkavalli, Ravi S.	365	185.29	02/16/2000
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	US-6,313,518	11/06/2001	Ahn, K. , et al.	257	632	03/02/2000
	US-6,337,805	01/08/2002	Forbes, Leonard , et al.	365	145	12/15/1999
	US-6,351,411	02/26/2002	Forbes, Leonard , et al.	365	182	06/12/2001
	US-6,368,941	04/09/2002	Chen, Tai-Ju , et al.	438	424	11/08/2000
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	US-6,391,769	05/21/2002	Lee, Jong-myeong , et al.	438	643	03/14/2000
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	US-6,432,779	08/13/2002	Hobbs, Christopher , et al.	438	287	01/30/2001
	US-6,438,031	08/20/2002	Fastow, Richard M.	365	185.18	10/26/2000
	US-6,444,039	09/03/2002	Nguyen, Tue	118	715	03/07/2000
	US-6,444,895	09/03/2002	Nikawa, Kiyoshi	136	212	09/24/1999
	US-6,445,023	09/03/2002	Vaartstra, Brian , et al.	257	295	03/16/1999
	US-6,445,030	09/03/2002	Wu, Yider , et al.	257	315	01/30/2001
	US-6,449,188	09/10/2002	Fastow, R.	365	185.18	06/19/2001
	US-6,456,531	09/24/2002	Wang, Janet S., et al.	365	185.18	06/19/2001
✓	US-6,456,536	09/24/2002	Sobek, Daniel , et al.	365	185.28	06/19/2001

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Group Art Unit	Unknown 2818
Examiner Name	Unknown PHAN

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TP	US-6,458,701	10/01/2002	Chae, Yun-sook , et al.	438	680	10/12/2000
	US-6,459,618	10/01/2002	Wang, Janet S.	365	185.18	06/13/2001
	US-6,465,334	10/15/2002	Buynoski, Matthew S., et al.	438	591	10/05/2000
	US-6,487,121	11/26/2002	Thurgate, Timothy J., et al.	365	185.18	07/05/2001
	US-6,495,436	12/17/2002	Ahn, Kie Y., et al.	438	591	02/09/2001
	US-6,498,362	12/24/2002	Forbes, Leonard , et al.	257	295	08/26/1999
	US-6,514,828	02/04/2003	Ahn, Kie Y., et al.	438	297	04/20/2001
	US-6,521,911	02/18/2003	Parsons, Gregory N., et al.	257	52	07/19/2001
	US-6,521,958	02/18/2003	Forbes, L. , et al.	257	391	08/26/1999
	US-6,534,420	03/18/2003	Ahn, Kie Y., et al.	438	768	07/18/2001
	US-6,545,314	04/08/2003	Forbes, Leonard , et al.			05/15/2001
	US-6,552,387	04/22/2003	Eitan, Boaz	257	324	12/14/1998
	US-6,559,014	05/06/2003	Jeon, J.	438	287	10/15/2001
	US-6,567,303	05/20/2003	Hamilton, D. G., et al.	365	185.03	01/16/2002
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✓	US-6,586,785	07/01/2003	Flagan, Richard C., et al.	257	261	06/29/2001

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
TP		ABBAS, S. A., et al., "N-Channel Igfet Design Limitations Due to Hot Electron Trapping", Technical Digest, International Electron Devices Meeting, Washington, DC, (December 1975), 35-38	
↓		ADELMANN, C , et al., "Atomic-layer epitaxy of GaN quantum wells and quantum dots on (0001) AlN", Journal of Applied Physics, 91(8), (April 15, 2002), 5498-5500	
↓		AHN, SEONG-DEOK , et al., "Surface Morphology Improvement of Metalorganic Chemical Vapor Deposition Al Films by Layered Deposition of Al and Ultrathin TiN", Japanese Journal of Applied Physics, Part 1 (Regular Papers, Short Notes & Review Papers), 39(6A), (June 2000), 3349-3354	

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Sheet 5 of 8	Attorney Docket No: 1303.058US2	

TP		AKASAKI, I. , "Effects of AlN Buffer Layer on Crystallographic Structure and on Electrical and Optical Properties of GaN and Ga(1-x)Al(x)N [0 < x (< or =) 0.4] Films Grown on Sapphire Substrate by MOVPE", <u>Journal of Crystal Growth</u> , 98, (1989),209-219	
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TP		FISCH, D E., et al., "Analysis of thin film ferroelectric aging", <u>Proc. IEEE Int. Reliability Physics Symp.</u> , (1990),237-242	
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	Application Number	Unknown 10/789,041
	Filing Date	Even Date Here with 2/27/04
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2818
	Examiner Name	Unknown PHAN
Sheet 8 of 8		Attorney Docket No: 1303.058US2

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